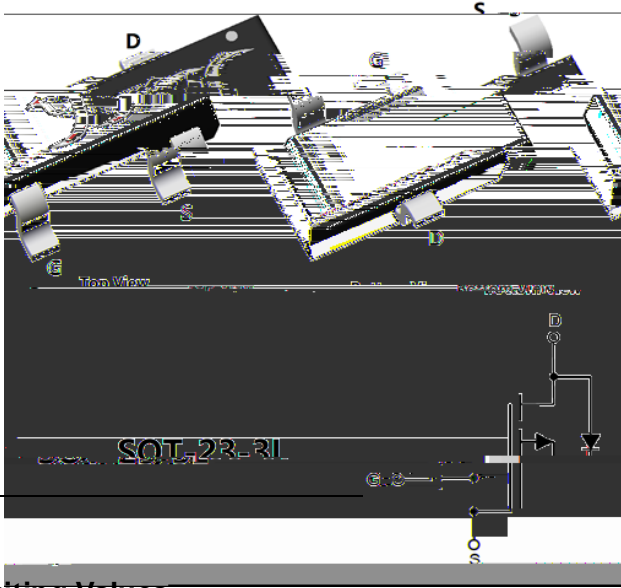




YJL072P06AL

P-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	-60V
I_D	-2.8A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	72m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	90m

General Description

- High density cell design for Low $R_{DS(ON)}$
- High Speed switching
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- PWM applications
- Power management
- Load switch

Limiting Values

Parameter	Conditions	Symbol	Min	Max	Unit
Drain-source Voltage	T_J 25°C; T_J 150°C	V_{DS}	-	-60	V
Gate-source Voltage	T_J 150°C; DC	V_{GS}	-20	20	
Continuous Drain Current (Note 1,2)	Steady-State $T_A=25$, $V_{GS}=-10V$ $T_A=100$, $V_{GS}=-10V$	I_D	-	-2.8	A
			-	-1.8	
Pulsed Drain Current	$T_A=25$, t 10 μ s	I_{DM}	-	-22	
Maximum Body-Diode Continuous Current	$T_A=25$	I_S		-1.2	
Total Power Dissipation (Note 1,2)	Steady-State $T_A=25$ $T_A=100$	P_D	-	1.06	W
			-	0.42	
Junction and Storage Temperature Range		T_J , T_{STG}	-55	150	

Thermal Resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	R_{JA}	-	117	mW

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL072P06AL		072AL	3000	30000	120000	



Typical Electrical and Thermal Characteristics Diagrams

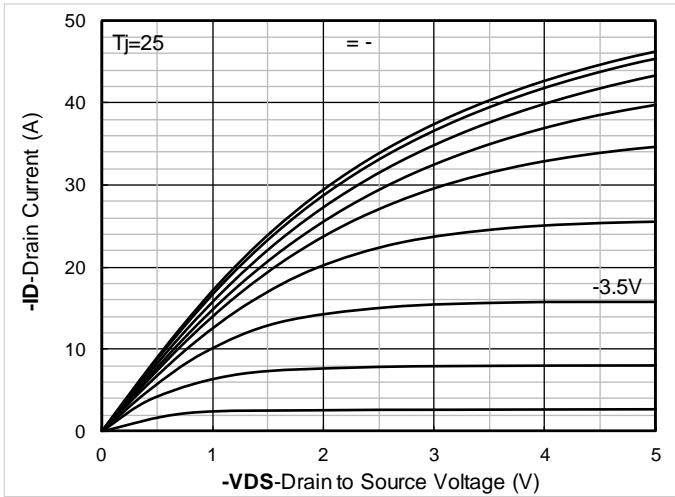


Figure 1. Output Characteristics; typical values

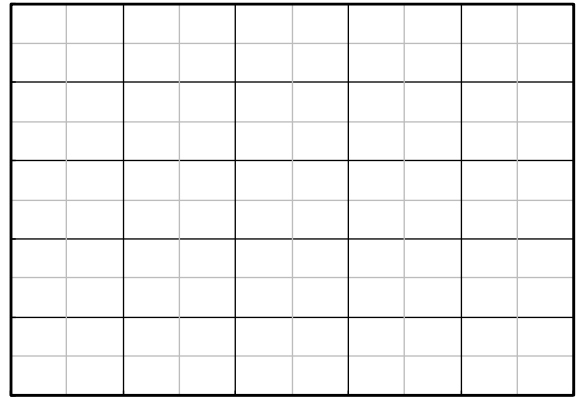


Figure 2. Transfer Characteristics; typical values

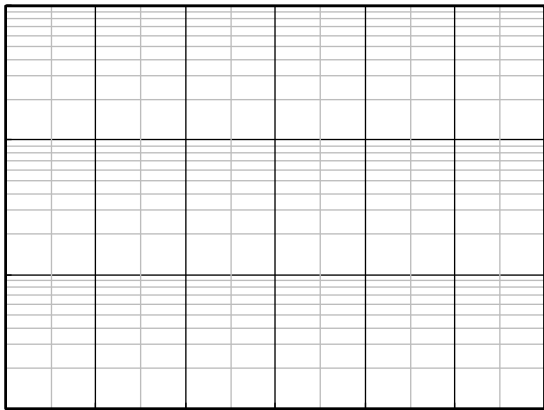


Figure 3. Capacitance Characteristics; typical values

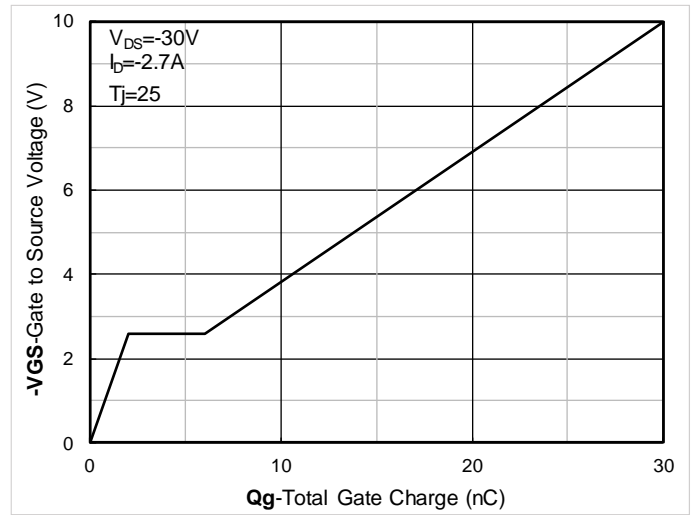


Figure 4. Gate Charge; typical values

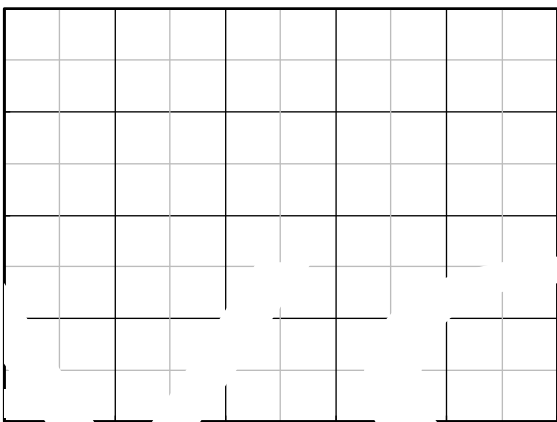
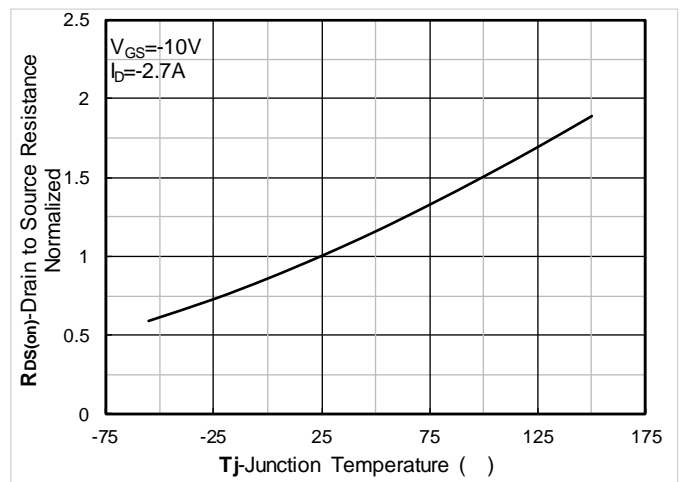


Figure 5. On-





YJL072P06AL

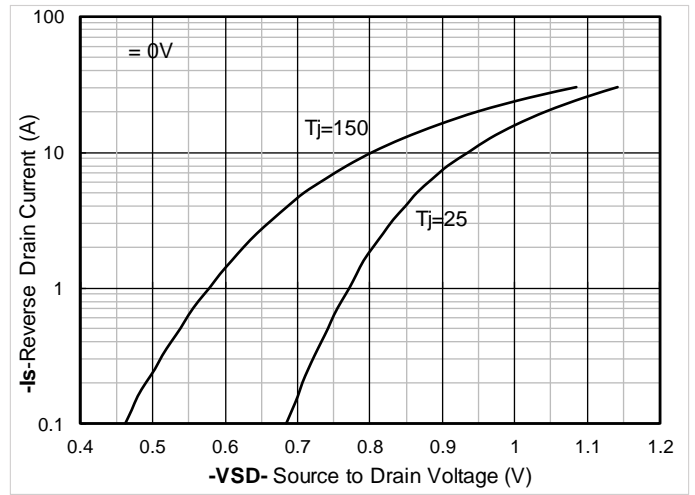
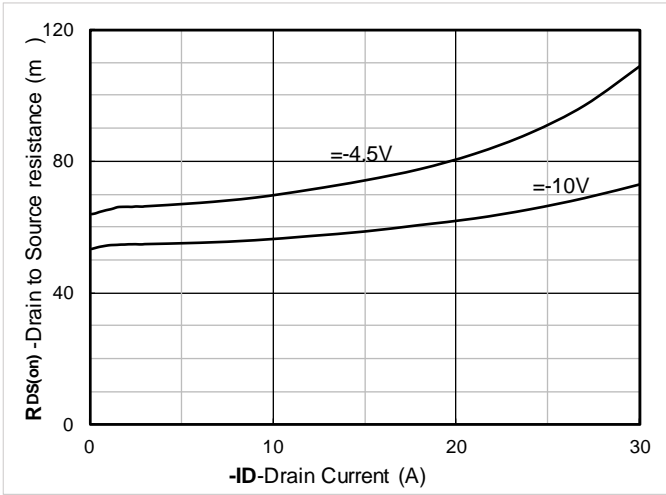


Figure 7. RDS(on) vs. Drain Current; typical values

Figure 8. Forward characteristics of reverse diode; typical values

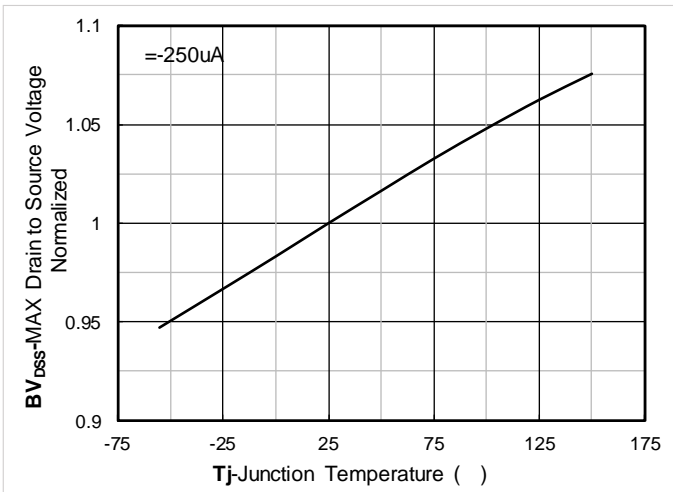


Figure 9. Normalized breakdown voltage

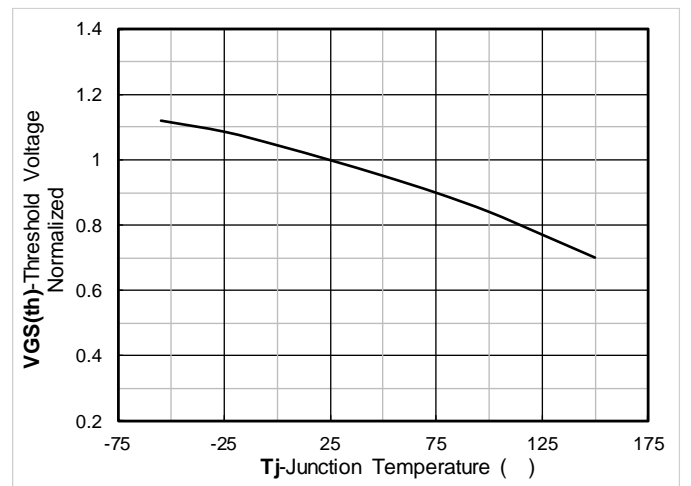


Figure 10. Normalized



SOT-23-3L Package Information

UNIT mm



Marking

